NSN 5961-01-372-8127

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-372-8127 **Inclosure Material:** Plastic **Overall Length:** 0.375 inches **Overall Width:** 0.340 inches **Component Name And Quantity:** 4 transistor **Mounting Method:** Terminal **Features Provided:** Electrostatic sensitive **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 80.0 breakdown voltage, collector-to-base, emitter open 4th transistor and 5.0 breakdown voltage, emitter-to-base, collector open 4th transistor and 50.0 breakdown voltage, collector-to-emitter, base open 4th transistor **Current Rating Per Characteristic:** 3.00 amperes collector current, dc all transistor **Power Rating Per Characteristic:** 10.0 watts total power dissipation 3rd transistor **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Terminal Type And Quantity:** 9 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: